



method 1  
 - only one FET!  
 - TX needs to be open-drain  
 - TX needs to sink high current (~12mA)  
 - sharp edges, bad for EMI  
 - struggles with <1k pullup and long bus  
 - other nodes need to pull close to 0V

method 2  
 - 2 BJTs (or FETs) and a diode  
 - TX can be weak push-pull (or open-drain)  
 - sharp edges, bad for EMI  
 - other nodes need to pull close to 0V

use 30k pullup instead of 1k if responder!

